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- (54) **Title:** EMBEDDED MEMORY IN INTERCONNECT STACK ON SILICON DIE

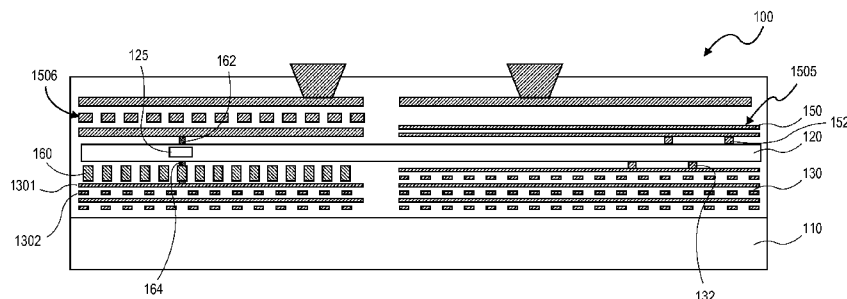


FIG. 1

- (57) **Abstract:** A method including forming a plurality of first interconnects and a plurality of second interconnects on opposite sides of an integrated circuit device layer including a plurality of circuit devices, wherein forming ones of the plurality of first interconnects and a plurality of second interconnects includes embedding memory devices therein. An apparatus including a substrate including a plurality of first interconnects and a plurality of second interconnects on opposite sides of an integrated circuit device layer including a plurality of circuit devices, wherein ones of the plurality of first interconnects and a plurality of second interconnects includes memory devices embedded therein.